

# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-40	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current, V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}\text{C (Note 6)}$ $T_A = +70^{\circ}\text{C (Note 6)}$ $T_A = +25^{\circ}\text{C (Note 5)}$	I <sub>D</sub>	-6.4 -5.1 -4.6	А
Maximum Body Diode Forward Current (Note 6)			Is	-5.2	Α
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	-21	Α
Pulsed Source Current (Note 7)			I <sub>SM</sub>	-21	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	2.0 16	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient	Steady state (Note 5)	D	62.5	°C/W
	Steady state (Note 6)	$R_{\theta JA}$	32	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μA	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	_	_	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance (Note 8)	D-s/s/iii			60	mΩ	$V_{GS} = -10V, I_D = -3.8A$	
Static Dialif-Source Off-Resistance (Note 6)	R <sub>DS(ON)</sub>	_	_	100		$V_{GS} = -4.5V, I_D = -2.9A$	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	-0.85	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.4A	
Forward Transconductance (Notes 8 & 10)	g <sub>fs</sub>	_	8.85	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.8A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1,007	_	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	130	_			
Reverse Transfer Capacitance	Crss	_	85	_			
Total Gate Charge (V <sub>GS</sub> = -5.0V)	$Q_g$	_	13.6	_		$V_{DS} = -20V, I_{D} = -3.8A,$	
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	_	26.1	_	nC		
Gate-Source Charge	Qgs	_	2.8	_	110		
Gate-Drain Charge	$Q_{gd}$	_	4.8	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.33	_		$V_{GS} = -10V$ , $V_{DD} = -20V$ , $R_G = 6.0\Omega$ , $I_{D} = -1.0A$	
Turn-On Rise Time	t <sub>r</sub>	_	8.84	_	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	29.18	_	113		
Turn-Off Fall Time	t <sub>f</sub>	_	12.54	_			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	27.2	_	nS	I <sub>F</sub> = -3A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		25.4	_	nC	ης = -3A, αι/αι = 100A/μS	

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on FR4 PCB measured at t ≤10 secs. 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width limited by maximum junction temperature. Notes:

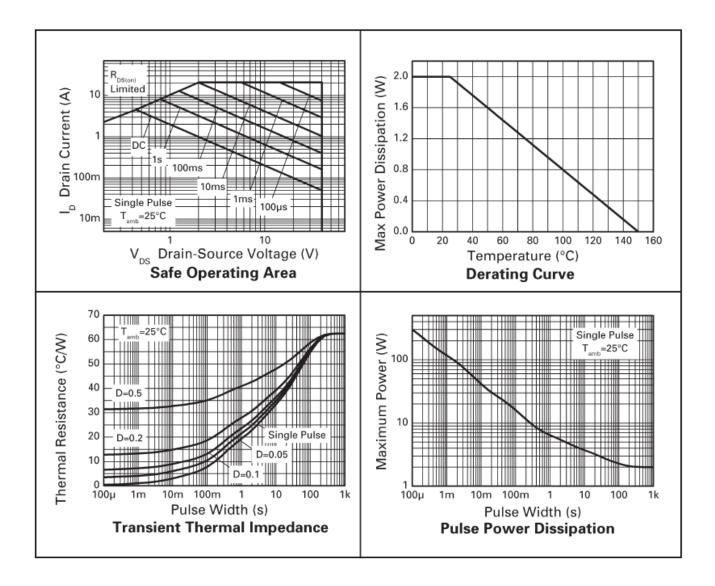
<sup>8.</sup> Measured under pulsed conditions. Width≤300µs. Duty cycle ≤ 2%.

<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.

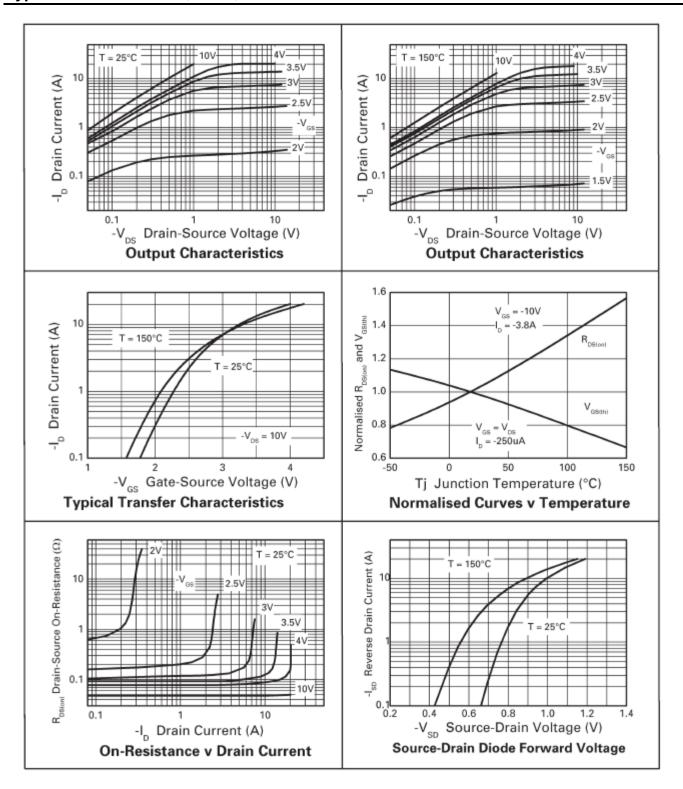


### **Typical Characteristics**



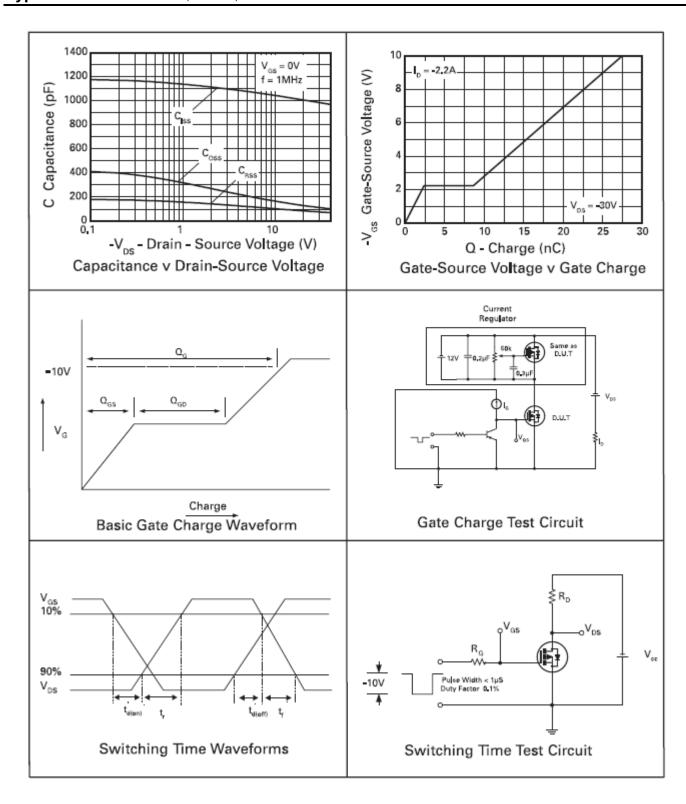


### Typical Characteristics (continued)





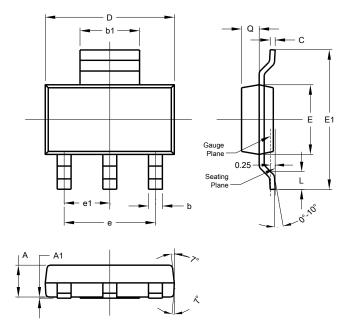
### Typical Characteristics (continued)





### **Package Outline Dimensions**

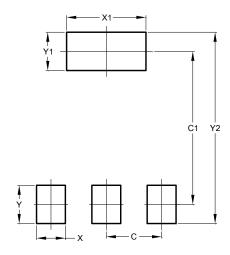
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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